HOPERF

RF Power Field Effect Transistor

HPM09S0P5N

N-Channel Enhancement-Mode MOSFET

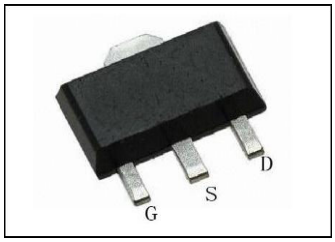
136–941 MHz, 0.5W, 7.5V BROADBAND RF POWER TRANSISTOR

Designed for handheld two–way radio applications with frequencies from 136 to 941 MHz. The high gain, ruggedness and Broadband performance of this device make it ideal for large–signal, common–source amplifier applications in handheld radio equipment.

Typical Broadband EVB Performance (I_{DQ}=50mA, T_A = 25℃, CW)

VDD	Freq.	Gmax	Pout		PAE
[V]	[MHz]	[dB]	[dBm]	[Watts]	[%]
7.5	400	19.8	28.3	0.67	59.6
	440	20.7	29.2	0.83	76.9
	480	21.0	28.9	0.77	74.6
	520	17.9	28.6	0.73	71.1

Capable of handling 20:1 VSWR @ 9Vdc, 0.8Watts, CW



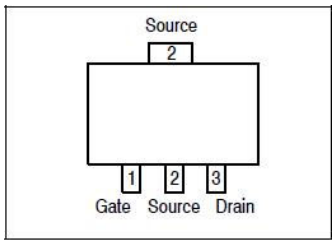


Figure 1. Pin Connections

Features

Characterized for Operation from 136 to 941 MHz

Unmatched Input and Output Allowing Broad Frequency Range Utilization

Integrated ESD Protection

Broadband – Full Power Across the Band

Exceptional Thermal Performance

Extreme Ruggedness

Typical Applications

Output Stage VHF Band Handheld Radio

Output Stage UHF Band Handheld Radio

Output Stage for 700–800 MHz Handheld Radio

Driver for 10–1000 MHz Applications

Table1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	–0.5, +20	Vdc
Gate-Source Voltage	V_{GS}	–0.5, +8	Vdc
Operating Voltage	V_{DD}	+0, +12	Vdc
Storage Temperature Range	T_{stg}	–65 to +150	℃
Case Operating Temperature	T_C	–40 to +150	℃
Operating Junction Temperature	T_J	–40 to +150	℃
Power Dissipation @TC=25℃	PD	3.0	Watts

Table 2. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22--A114)	2, passes 2500 V
Machine Model (per EIA/JESD22--A115)	A, passes 100 V
Charge Device Model (per JESD22--C101)	IV, passes 2000 V

Table 3. Electrical Characteristics (T_A=25℃ unless otherwise noted)

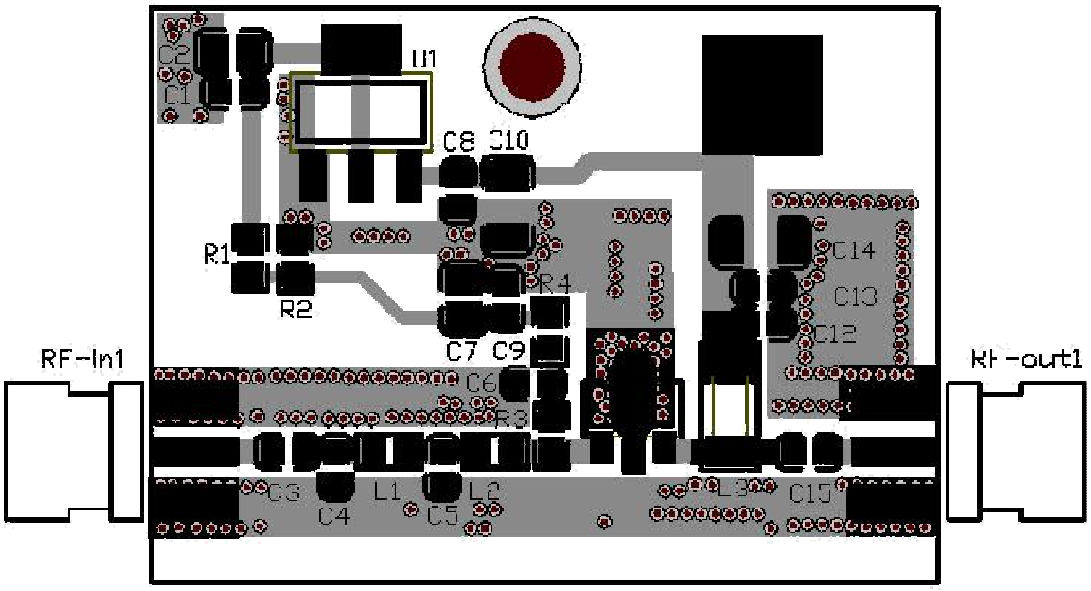
Characteristic	Symbol	Min	Typ.	Max	Unit
Off Characteristics					
Gate-Source Leakage Current (V_{GS}=5Vdc, V_{DS}=0Vdc)	I_{GSS}	-	-	500	nAdc
Zero Gate Voltage Drain Leakage Current (V_{DS}=16Vdc, V_{GS}=0Vdc)	I_{DSS}	-	-	1	uAdc
Zero Gate Voltage Drain Leakage Current (V_{DS}=7.5Vdc, V_{GS}=0Vdc)	I_{DSS}	-	-	500	nAdc
On Characteristics					
Gate Threshold Voltage (V_{DS}=7.5Vdc, I_D=1mA)	$V_{GS(th)}$	1.6	1.8	2.0	Vdc
Gate Quiescent Voltage (V_{DD}=7.5Vdc, I_D=50mA Measured in Functional Test)	$V_{GS(Q)}$	2.2	2.4	2.8	Vdc
Drain-Source On-Voltage (V_{GS}=5Vdc, I_D=100mA)	$V_{DS(ON)}$	-	0.25	-	Vdc
Dynamic Characteristics					
Reverse Transfer Capacitance (V_{DG}=7.5V, Level=30mVac@1MHz)	Crss	-	0.21	-	pF
Output Capacitance (V_{DS}=7.5V, Level=30mVac@1MHz)	Coss	-	1.6	-	pF
Input Capacitance (V_{GS}=5V, Level=30mVac@1MHz)	Ciss	-	8.0	-	pF

Typical Performances (In DuSemi Narrowband Test DEMO, 50 Ohm system)

Frequency=440MHz, VDD=7.5Vdc, $I_{D(Q)}$=50mA, Pin=9dBm, T_A=25℃

Output Power	P_{out}	-	0.61	-	Watts
Power Gain	G_{PS}	-	19.0	-	dB
Drain Efficiency	η_D	-	66.5	-	%

Broad Band Evaluation Circuit (@VDD = 7.5V, f = 440 MHz)



Test Circuit Component Layout

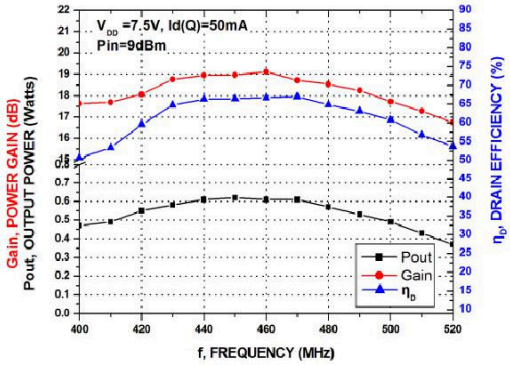
Table 4. Test Circuit Component Designations and Value

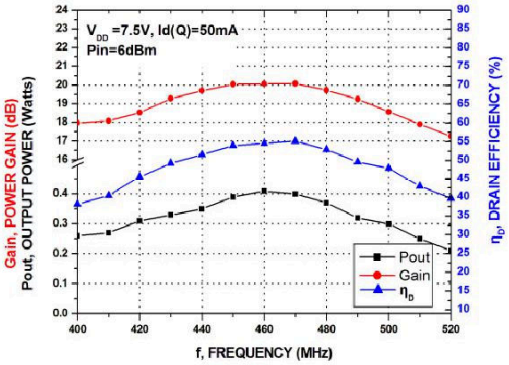
Part	Description	Part Number	Manufacturer
R3	470Ohm	—	—
R4	6.8KOhm	—	—
L1, L2	4.7nH	—	—
L3	8 Turns D: 0.5 mm, φ 2.4 mm Enamel Wire	—	—
C3,C15,	100pF Chip Capacitors	GQM21P5C1H101JB01	Murata
C4	18pF Chip Capacitors	GRM1885C1H201JA01	Murata
C12, C9	1000pF Chip Capacitors	GRM1885C1H102JA01	Murata
C10, C14,C7	10uF,25VChip Capacitors	—	—
C5	24pF Chip Capacitors	—	Murata
R1,R2,C1,C2,C8,C6	NC	—	—
U1	LM1117		
PCB	FR-4 ,1.6mm, ε_r4.5	—	—

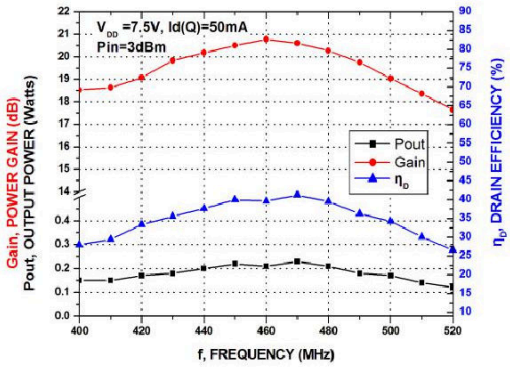
TYPICAL CHARACTERISTICS

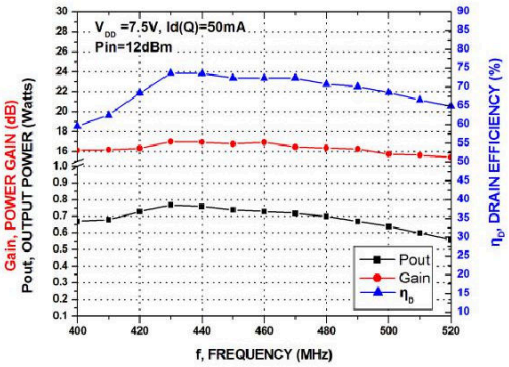
1、Power Gain, Drain Efficiency and Output Power versus Frequency at a Constant Pin

V_{DD}	$I_{D(Q)}$	Pin	Freq	Pout		Gain	η_D
[V]	[mA]	[dBm]	[MHz]	[dBm]	[Watts]	[dB]	[%]
7.5	50	9	400	26.7	0.47	17.6	50.7
			440	27.9	0.61	19.0	66.5
			480	27.6	0.57	18.5	64.8
			520	25.7	0.37	16.8	53.7

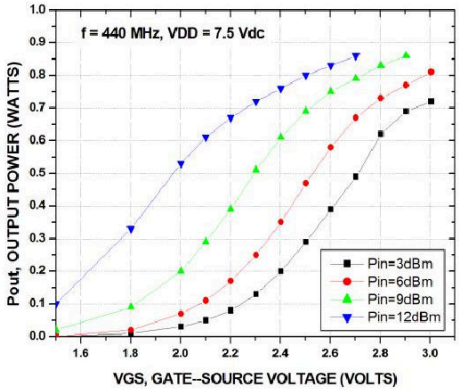






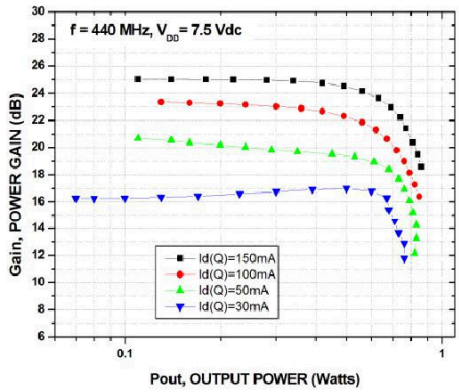


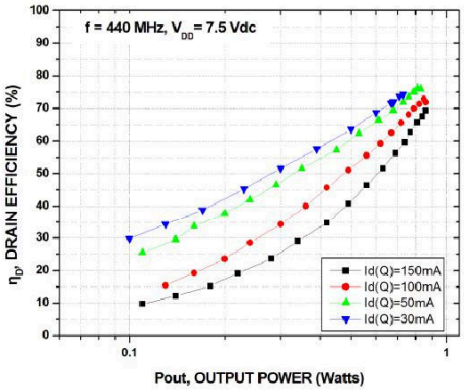
2. Output Power versus Gate-Source Voltage @440MHz



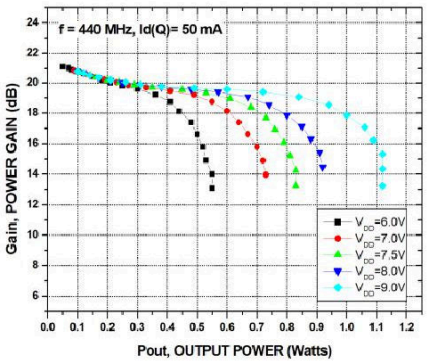
3. Power Gain and Drain Efficiency versus Output Power@440MHz

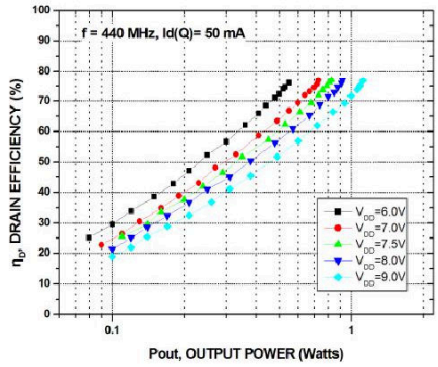
Freq	V_{DD}	$I_{D(Q)}$	Pout		Gain	PAE
[MHz]	[V]	[mA]	[dBm]	[Watts]	[dB]	[%]
440	7.5	30	28.8	0.76	17.0	74.4
		50	29.2	0.83	20.7	76.9
		100	29.4	0.87	23.8	73.4
		150	29.5	0.89	25.6	69.3





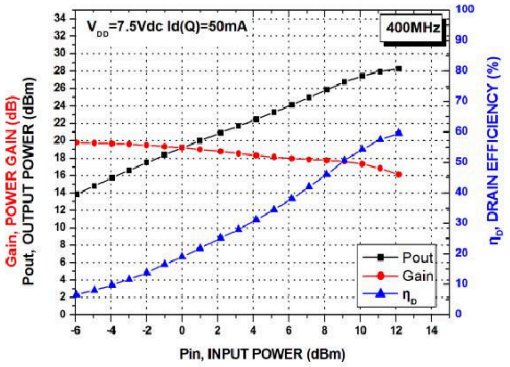
Freq	$I_{D(Q)}$	V_{DD}	Pout		Gain	PAE
[MHz]	[mA]	[V]	[dBm]	[Watts]	[dB]	[%]
440	50	6.0	27.4	0.55	21.0	76.6
		7.0	28.6	0.73	20.8	76.7
		7.5	29.2	0.83	20.7	76.9
		8.0	29.6	0.92	20.8	76.8
		9.0	30.5	1.12	20.8	76.7

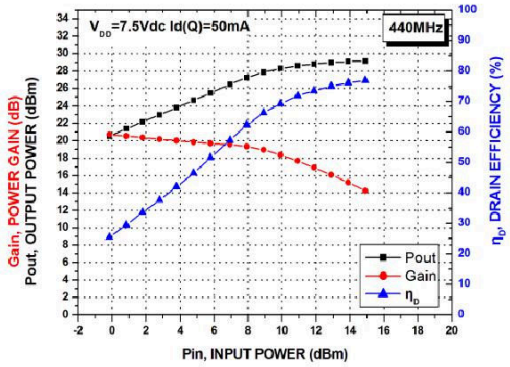


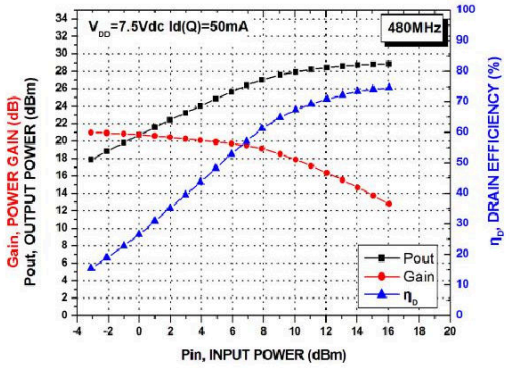


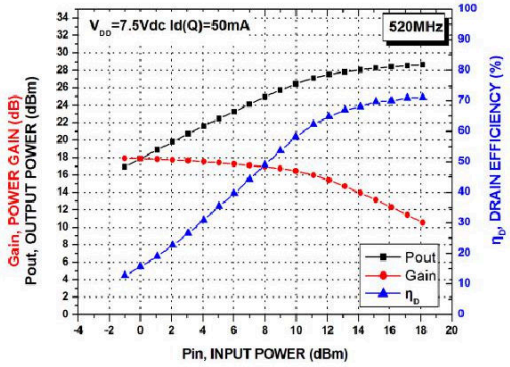
4. Power Gain, Drain Efficiency and Output Power versus Input Power

V_{DS}	$I_{D(Q)}$	Freq.	Gain	Pout		η_D
[V]	[mA]	[MHz]	[dB]	[dBm]	[Watts]	[%]
7.5	50	400	19.8	28.3	0.67	59.6
		440	20.7	29.2	0.83	76.9
		480	21.0	28.9	0.77	74.6
		520	17.9	28.6	0.73	71.1

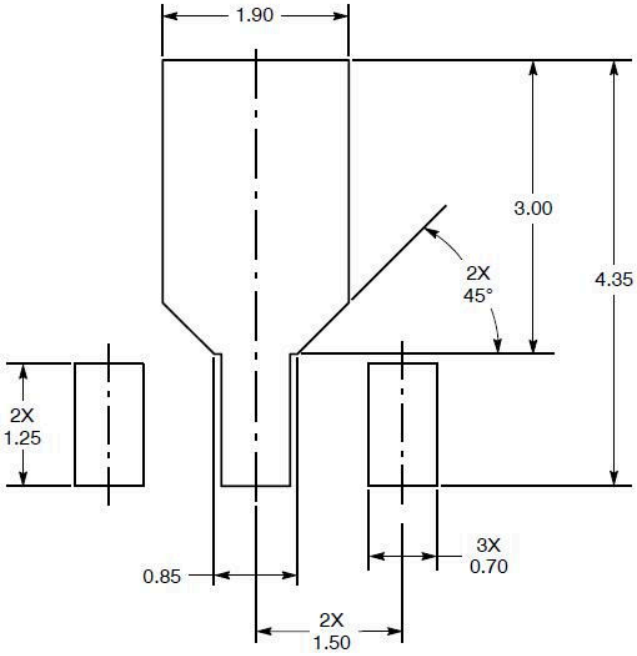




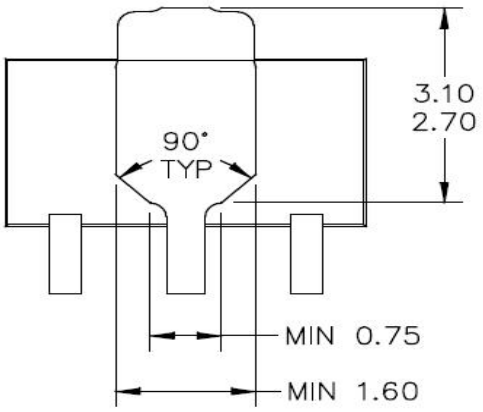




PACKAGE
Unit : mm

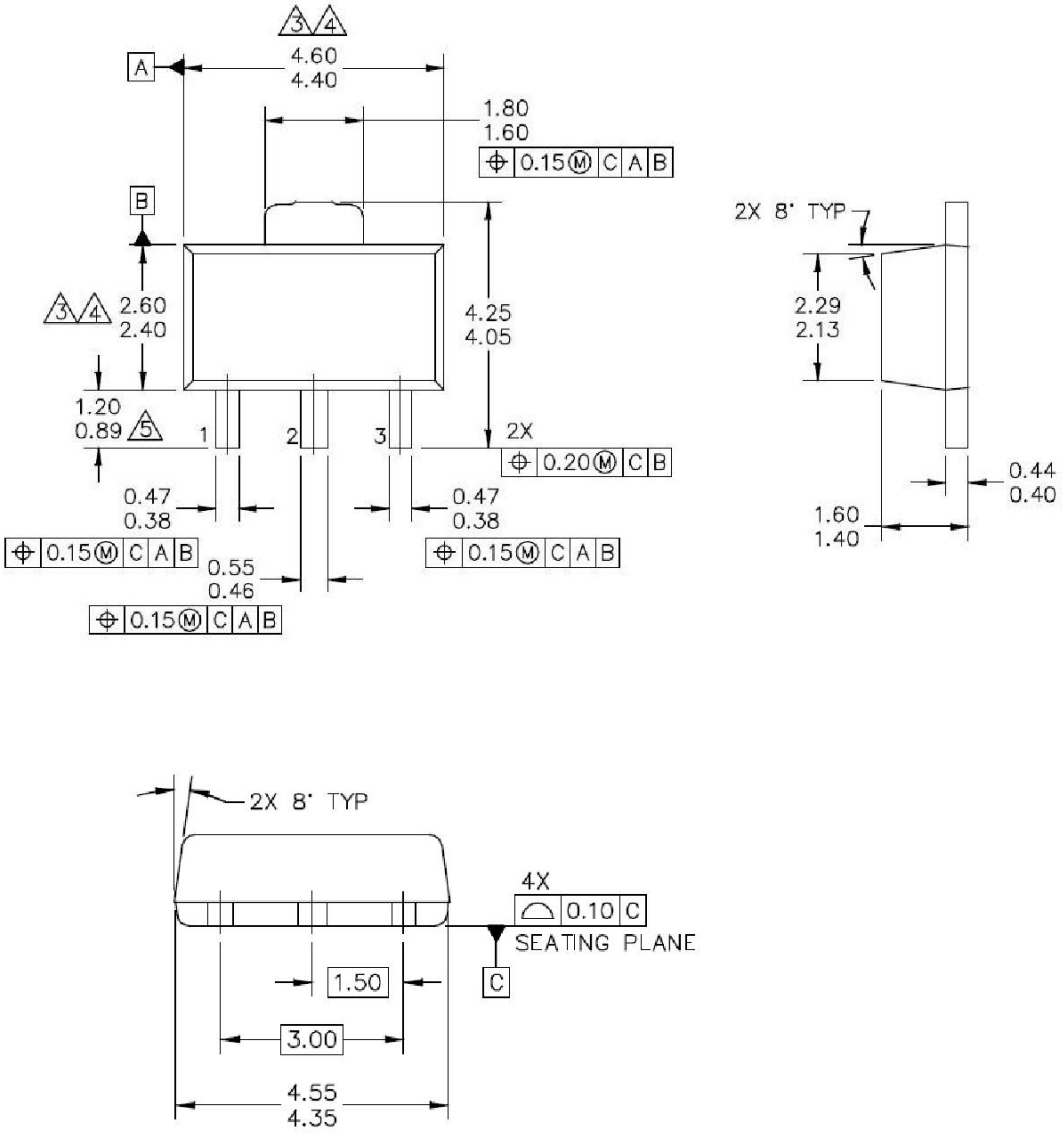


PCB Pad Layout for SOT– 89



Bottom View

PACKAGE DIMENSIONS



REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
1.0	March 2018	Initial Release of Data Sheet